

BGA3018 1 GHz 18 dB gain wideband amplifier MMIC Rev. 3 – 26 September 2013

Product data sheet

1. Product profile

1.1 General description

The BGA3018 MMIC is a wideband amplifier with internal biasing. It is designed specifically for high linearity CATV line extenders and drop amplifiers over a frequency range of 5 MHz to 1006 MHz. The LNA is housed in a lead free 3-pin SOT89 package.

Noise figure of 2.1 dB

75 Ω input and output impedance

1.2 Features and benefits

- Internally biased
- Flat gain
- High linearity with an IP3_O of 40 dBm and
 Operating from 5 V to 8 V supply an IP2_O of 60 dBm

1.3 Applications

- General wideband amplifiers.
- CATV return amplifier; frequency ranges of 5 MHz to 300 MHz.
- CATV infrastructure network driver in optical nodes (FTTx), distribution amplifiers, trunk amplifiers and line extenders in the frequency range from 40 MHz to 1006 MHz.
- The product is ideally suited for applications as drop amplifiers in CATV distribution systems such as FTTH

1.4 Quick reference data

Table 1. Quick reference data

Bandwidth 40 MHz to 1006 MHz; $T_{amb} = 25 \ ^{\circ}C$; typical values at $V_{CC} = 8 \ V$; $Z_S = Z_L = 75 \ \Omega$; $R1 = 470 \ \Omega$; $R2 = 300 \ \Omega$.

Symbol	Parameter	Conditions	Μ	lin	Тур	Мах	Unit
V _{CC}	supply voltage	RF input AC coupled	7.	.6	8	8.4	V
I _{CC(tot)}	total supply current		-		120	135	mA
T _{amb}	ambient temperature		-4	40	-	+85	°C
NF	noise figure	f = 500 MHz	-		2.1	2.6	dB
P _{L(1dB)}	output power at 1 dB gain compression		23	3.5	25	-	dBm
IP3 ₀	output third-order intercept point		<mark>[1]</mark> 3(6	40	-	dBm
IP2 ₀	output second-order intercept point		[2] _		60	-	dBm

[1] The fundamental frequencies (f_1) and (f_2) lay between 40 MHz and 1006 MHz. The intermodulation product (IM3) is 2 × $f_2 - f_1$, where $f_2 = f_1 \pm 6$ MHz. Input power $P_i = -20$ dBm.

[2] The fundamental frequencies (f_1) and (f_2) lay between 40 MHz and 1006 MHz. The intermodulation product (IM2) is $|f_2 - f_1|$, with 40 MHz < $|f_1-f_2|$ < 1006 MHz. Input power $P_i = -20$ dBm.



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2. Pinning information

Table 2.	Pinning			
Pin	Description	Sin	nplified outline	Graphic symbol
1	RF_OUT and biasing	<u>[1]</u>		
2	GND	[2]		
3	RF_IN	[1]		3 12 5 5 5 5 5 5 5 5 7 130

[1] This pin is DC-coupled and requires an external DC-blocking capacitor.

[2] The center metal base of the SOT89 also functions as heatsink for the power amplifier.

3. Ordering information

ing informa	tion	
Package		
Name	Description	Version
-	plastic surface-mounted package; exposed die pad for good heat transfer; 3 leads	SOT89
EVB	1 GHz 18 dB gain wideband amplifier application	-
EVB	5 MHz to 300 MHz 18 dB reverse amplifier application	-
EVB	40 MHz to 1006 MHz push-pull amplifier application	-
EVB	BGA301x wideband variable gain amplifier application	-
	Package Name - EVB EVB EVB	NameDescription-plastic surface-mounted package; exposed die pad for good heat transfer; 3 leadsEVB1 GHz 18 dB gain wideband amplifier applicationEVB5 MHz to 300 MHz 18 dB reverse amplifier applicationEVB40 MHz to 1006 MHz push-pull amplifier application

4. Marking

Table 4. Marking codes		
Type number	Marking code	Description
BGA3018	*6Y	* = W : made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage	RF input AC coupled	-0.6	+15	V
Pi	input power	single tone	-	20	dBm
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-40	+85	°C
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E	2	-	kV
		Charged Device Model (CDM); According JEDEC standard 22-C101B	2	-	kV

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6. Thermal characteristics

Table 6.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		40	K/W

7. Characteristics

7.1 Forward application

Table 7. Characteristics at V_{CC} = 8 V

Bandwidth 40 MHz to 1006 MHz; $T_{amb} = 25 \ ^{\circ}C$; typical values at $V_{CC} = 8 \ V$; $Z_S = Z_L = 75 \ \Omega$; $R1 = 470 \ \Omega$; $R2 = 300 \ \Omega$.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CC}	supply voltage	RF input AC coupled		7.6	8	8.4	V
I _{CC(tot)}	total supply current			-	120	135	mA
$ s_{21} ^2$	insertion power gain			17	18	19	dB
$\mathrm{SL}_{\mathrm{sl}}$	slope straight line			-	0.5	-	dB
FL	flatness of frequency response			-	0.5	-	dB
NF	noise figure	f = 50 MHz		-	1.9	2.4	dB
		f = 500 MHz		-	2.1	2.6	dB
		f = 1000 MHz		-	2.5	3.0	dB
RL _{in}	input return loss	f = 50 MHz		-	18.5	-	dB
		f = 500 MHz		-	20	-	dB
		f = 1000 MHz		-	28	-	dB
RL _{out}	output return loss	f = 50 MHz		-	24	-	dB
		f = 500 MHz		-	28	-	dB
		f = 1000 MHz		-	16	-	dB
P _{L(1dB)}	output power at 1 dB gain compression			23.5	25	-	dBm
IP3 ₀	output third-order intercept point		[1]	36	40	-	dBm
IP2 ₀	output second-order intercept point		[2]	-	60	-	dBm
СТВ	composite triple beat		[3]	-	-75	-	dBc
CSO	composite second-order distortion		[3]	-	-60	-	dBc

[1] The fundamental frequencies (f_1) and (f_2) lay between 40 MHz and 1006 MHz. The intermodulation product (IM3) is $2 \times f_2 - f_1$, where $f_2 = f_1 \pm 6$ MHz. Input power $P_i = -20$ dBm.

[2] The fundamental frequencies (f_1) and (f_2) lay between 40 MHz and 1006 MHz. The intermodulation product (IM2) is $|f_2 - f_1|$, with 40 MHz < $|f_1 - f_2|$ < 1006 MHz. Input power $P_i = -20$ dBm.

[3] Measured with 132 NTSC channels $V_0 = 30 \text{ dBmV}$.

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Table 8.	Characteristics at V _{CC} = 5 V	
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Bandwidth 40 MHz to 1006 MHz; $T_{amb} = 25 \ ^{\circ}C$; typical values at $V_{CC} = 5 \ V$; $Z_S = Z_L = 75 \ \Omega$; $R1 = 470 \ \Omega$; $R2 = 300 \ \Omega$.

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Symbol	Parameter	Conditions	Mi	in	Тур	Max	Unit
V _{CC}	supply voltage	RF input AC coupled	4.	75	5	5.25	V
I _{CC(tot)}	total supply current		-		75	85	mA
$ s_{21} ^2$	insertion power gain		-		18	-	dB
SL _{sl}	slope straight line		-		0.5	-	dB
FL	flatness of frequency response		-		0.5	-	dB
NF	noise figure	f = 50 MHz	-		1.9	-	dB
		f = 500 MHz	-		2.2	-	dB
		f = 1000 MHz	-		2.5	-	dB
RL _{in}	input return loss	f = 50 MHz	-		18.5	-	dB
		f = 500 MHz	-		18.5	-	dB
		f = 1000 MHz	-		28	-	dB
RL _{out}	output return loss	f = 50 MHz	-		26	-	dB
		f = 500 MHz	-		28	-	dB
		f = 1000 MHz	-		16	-	dB
P _{L(1dB)}	output power at 1 dB gain compression		-		18	-	dBm
IP3 ₀	output third-order intercept point		<u>[1]</u> -		36	-	dBm
IP2 ₀	output second-order intercept point		[2] _		54	-	dBm
СТВ	composite triple beat		[3] _		-70	-	dBc
CSO	composite second-order distortion		[3] _		-54	-	dBc

[1] The fundamental frequencies (f₁) and (f₂) lay between 40 MHz and 1006 MHz. The intermodulation product (IM3) is $2 \times f_2 - f_1$, where $f_2 = f_1 \pm 6$ MHz. Input power $P_i = -20$ dBm.

[2] The fundamental frequencies (f_1) and (f_2) lay between 40 MHz and 1006 MHz. The intermodulation product (IM2) is $|f_2 - f_1|$, with 40 MHz < $|f_1 - f_2| < 1006$ MHz. Input power $P_i = -20$ dBm.

[3] Measured with 132 NTSC channels $V_0 = 30$ dBmV.

7.2 Return application

Table 9.Characteristics at V_{CC} = 8 V

Bandwidth 5 MHz to 300 MHz; $T_{amb} = 25 \,^{\circ}$ C; typical values at $V_{CC} = 8 \,^{\circ}$ V; $Z_S = Z_L = 75 \,^{\circ}$ C; $R1 = 470 \,^{\circ}$ C; $R2 = 300 \,^{\circ}$ C.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage	RF input AC coupled	7.6	8	8.4	V
I _{CC(tot)}	total supply current		-	120	135	mA
$ s_{21} ^2$	insertion power gain		-	18	-	dB
SL _{sl}	slope straight line		-	0.5	-	dB
FL	flatness of frequency response		-	0.5	-	dB
NF	noise figure	f = 50 MHz	-	1.9	-	dB
RL _{in}	input return loss	f = 5 MHz	-	18.5	-	dB
		f = 100 MHz	-	18.5	-	dB
		f = 200 MHz	-	18.5	-	dB
		f = 300 MHz	-	18.5	-	dB
RL _{out}	output return loss	f = 5 MHz	-	18.5	-	dB
		f = 100 MHz	-	18.5	-	dB
		f = 200 MHz	-	18.5	-	dB
		f = 300 MHz	-	18.5	-	dB
P _{L(1dB)}	output power at 1 dB gain compression		-	25	-	dBm
IP3 ₀	output third-order intercept point		<u>[1]</u> _	40	-	dBm
IP2 ₀	output second-order intercept point		[2] _	60	-	dBm

[1] The fundamental frequencies (f₁) and (f₂) lay between 5 MHz and 300 MHz. The intermodulation product (IM3) is $2 \times f_2 - f_1$, where $f_2 = f_1 \pm 6$ MHz. Input power $P_i = -20$ dBm.

[2] The fundamental frequencies (f₁) and (f₂) lay between 5 MHz and 300 MHz. The intermodulation product (IM2) is $|f_2 - f_1|$, with 40 MHz $< |f_1-f_2| < 300$ MHz. Input power P_i = -20 dBm.

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Table 10.	Characteristics at V _{CC} =	: 5 V
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Bandwidth 5 MHz to 300 MHz; $T_{amb} = 25 \ ^{\circ}C$; typical values at $V_{CC} = 5 \ V$; $Z_S = Z_L = 75 \ \Omega$; $R1 = 470 \ \Omega$; $R2 = 300 \ \Omega$.

	, · ·					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage	RF input AC coupled	4.75	5	5.25	V
I _{CC(tot)}	total supply current		-	75	85	mA
$ s_{21} ^2$	insertion power gain		-	18	-	dB
SL _{sl}	slope straight line		-	0.5	-	dB
FL	flatness of frequency response		-	0.5	-	dB
NF	noise figure	f = 50 MHz	-	1.9	-	dB
RL _{in}	input return loss	f = 5 MHz	-	18.5	-	dB
		f = 100 MHz	-	18.5	-	dB
		f = 200 MHz	-	18.5	-	dB
		f = 300 MHz	-	18.5	-	dB
RL _{out}	output return loss	f = 5 MHz	-	18.5	-	dB
		f = 100 MHz	-	18.5	-	dB
		f = 200 MHz	-	18.5	-	dB
		f = 300 MHz	-	18.5	-	dB
P _{L(1dB)}	output power at 1 dB gain compression		-	20	-	dBm
IP3 ₀	output third-order intercept point		<u>[1]</u> -	36	-	dBm
IP2 ₀	output second-order intercept point		[2] _	54	-	dBm

[1] The fundamental frequencies (f₁) and (f₂) lay between 5 MHz and 300 MHz. The intermodulation product (IM3) is $2 \times f_2 - f_1$, where $f_2 = f_1 \pm 6$ MHz. Input power P_i = -20 dBm.

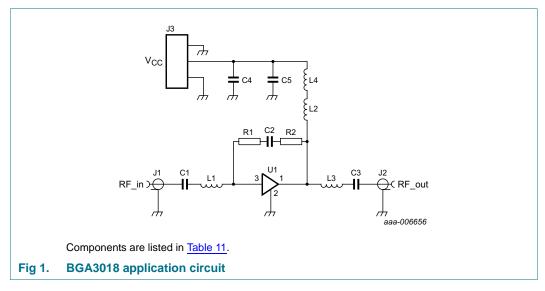
[2] The fundamental frequencies (f₁) and (f₂) lay between 5 MHz and 300 MHz. The intermodulation product (IM2) is $|f_2 - f_1|$, with 40 MHz < $|f_1 - f_2|$ < 300 MHz. Input power P_i = -20 dBm.

8. Application information

8.1 Forward application 40 MHz to 1006 MHz

The BGA3018 can be used in other applications. Please contact your local sales representative for more information. Application notes are available on the NXP website.

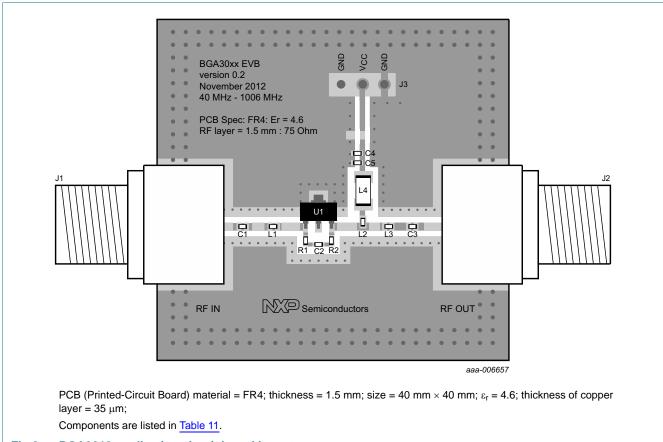
8.1.1 Forward application circuit



All control and supply lines must be decoupled properly. The decoupling capacitors must be placed as close to the device as possible.

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8.1.2 Forward application circuit board layout

Fig 2. BGA3018 application circuit board layout

Table 11. List of components See Figure 1 and Figure 2

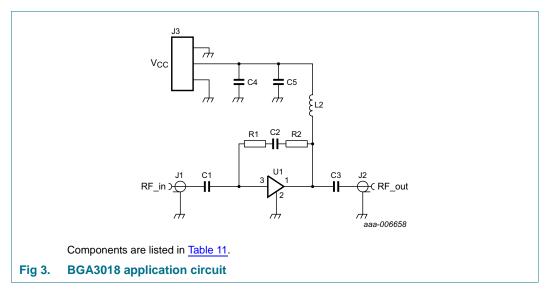
See <u>Figure 1</u> and <u>Figure 2</u>.

Component	Description	Value	Size	Remarks
C1, C2, C3, C4	capacitor	10 nF	SMD 0402	Murata GRM155R71E103KA01D or capacitor of same quality
C5	capacitor	100 pF	SMD 0402	Murata GRM1555C1H101JZ01D or capacitor of same quality
J1, J2	F-connector	75 Ω	-	Bomar 861V509ER6 or F-connector of same quality
J3	header 3-way	-	-	Molex 90121-0763 or header of the same quality
L1, L3	inductor	3.9 nH	SMD 0402	Murata LQG15HS3N9S02D or inductor of same quality
L2	choke	-	SMD 0603	Murata BLM18HD182SN1D or choke of same quality
L4	inductor	880 nH	SMD 1206	Murata LQH31HNR88K03L or inductor of same quality
R1	resistor	470 Ω	SMD 0402	Yageo RC0402FR-07470RL or resistor of same quality
R2	resistor	300 Ω	SMD 0402	Yageo RC0402FR-07300RL or resistor of same quality
U1	BGA3018	-	-	NXP

8.2 Return application 5 MHz to 300 MHz

The BGA3018 can be used in other applications. Please contact your local sales representative for more information. Application notes are available on the NXP website.

8.2.1 Return application circuit

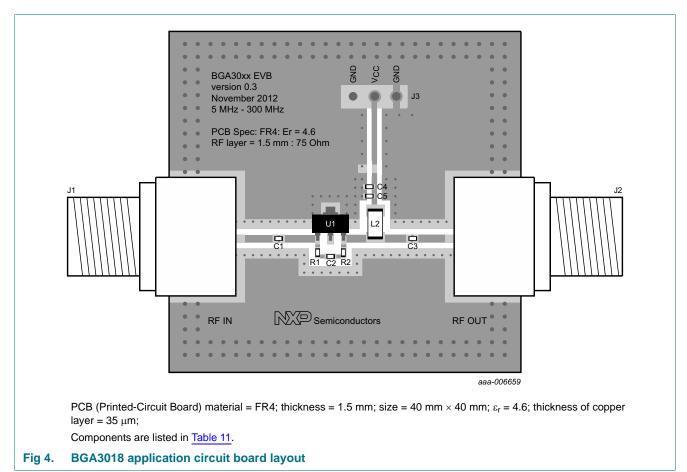


All control and supply lines must be decoupled properly. The decoupling capacitors must be placed as close to the device as possible.

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8.2.2 Return application circuit board layout

Table 12.List of componentsSee Figure 1 and Figure 2.

Component C1, C2, C3, C4	Description capacitor	Value	Size	Remarks
01.02.03.04		10 nF	SMD 0402	Murata GRM155R71E103KA01D or capacitor of same quality
	•	-		· · · · ·
C5	capacitor	100 pF	SMD 0402	Murata GRM1555C1H101JZ01D or capacitor of same quality
J1, J2	F-connector	75 Ω	-	Bomar 861V509ER6 or F-connector of same quality
J3	header 3-way	-	-	Molex 90121-0763 or header of the same quality
L2	inductor	22 µH	SMD 1206	Murata LQH31CN220K03L or inductor of same quality
R1	resistor	470 Ω	SMD 0402	Yageo RC0402FR-07470RL or resistor of same quality
R2	resistor	300 Ω	SMD 0402	Yageo RC0402FR-07300RL or resistor of same quality
U1	BGA3018	-	-	NXP

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9. Package outline

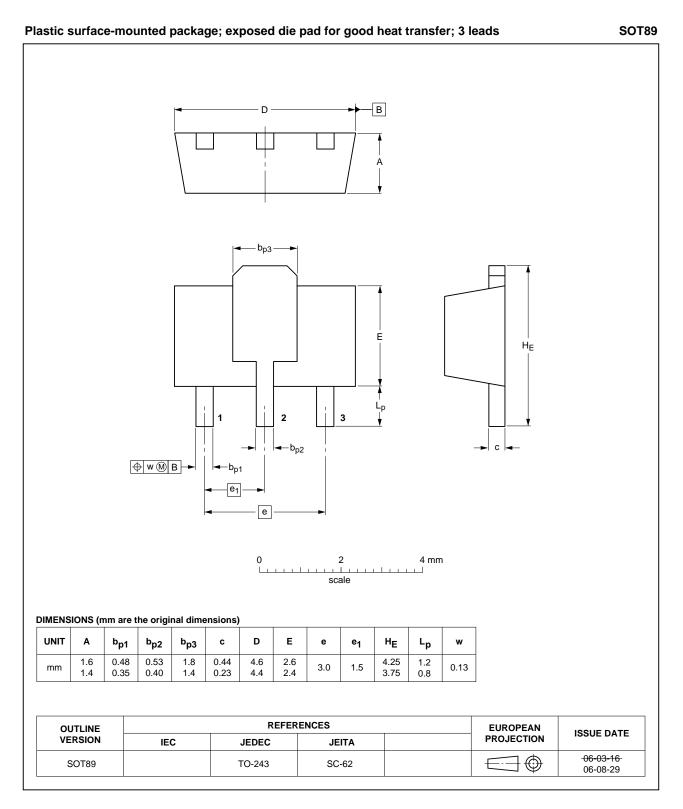


Fig 5. Package outline SOT89 (SC-62)

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BGA3018

10. Abbreviations

Table 13. Abbreviations				
Acronym	Description			
CATV	Community Antenna TeleVision			
FTTH	Fiber To The Home			
FTTx	Fiber To The "x"			
LNA	Low-Noise Amplifier			
MMIC	Monolithic Microwave Integrated Circuit			

11. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGA3018 v.3	20130926	Product data sheet	-	BGA3018 v.2
Modifications:	• Table 3 on p	bage 2: Evaluation boards ha	ave been added.	
BGA3018 v.2	20130415	Product data sheet	-	BGA3018 v.1
BGA3018 v.1	20130319	Preliminary data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

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